

深圳市晶泰源电子有限公司

JTY B772

TRANSISTOR(PNP)

FEATURES

Power dissipation

PCM:1W(Tamb=25°C)

Collector current

ICM:-2.0A

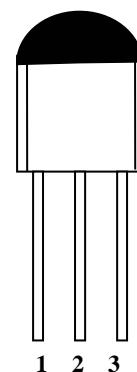
Collector-base voltage

V(BR)CBO: -40V

Operating and storage junction temperature range

TJ,Tstg:-65°C to -150°C

T0-92



1. Emitter

2. Collector

3. Base

ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	Ic=-1mA, Ie=0	-40			V
Collector-emitter breakdown voltage	V(BR)CEO	Ic=-1mA, Ib=0	-30			V
Emitter-base breakdown voltage	V(BR)EBO	Ic=-1mA, Ic=0	-6			V
Collector cut-off current	Icbo	Vcb=-40V, Ie=0			-0.5	μA
Collector cut-off current	Iceo	Vce=-30V, Ib=0			-1.0	μA
Emitter cut-off current	Ieb0	Veb=-6V, Ic=0			-0.1	μA
DC current gain	Hfe	Vce=-5V, Ic=-1mA	200		400	
Collector-emitter saturation voltage	Vce(sat)	Ic=-2A, Ib=-200mA			-0.5	V
Base-emitter saturation voltage	Vbe(sat)	Ic=-2A, Ib=-200mA			-2.0	V
Transition frequency	fT	Vce=10V, Ic=50mA f=30MHz	50			MHZ

CLASSIFICATION OF hFE(2)

Rank	P	
Range	300-400	

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